

Vanishing atomic migration barrier in SiO₂

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Stability of Solid State Reaction Fronts. Physical Review Letters, 1998, 81, 2490-2493.	7.8	17
2	Effect of Particle Size on Rate of Coalescence of Silica Nanoparticles. Journal of Colloid and Interface Science, 1999, 213, 258-261.	9.4	31
3	Structuring thin films via ion beams. , 2000, , 407-421.		0
4	On Kinetically vs. Energetically Driven Growth Instabilities in Solid and Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2000, 618, 233.	0.1	0
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7	Morphological instability of growth fronts due to stress-induced mobility variations. Applied Physics Letters, 2000, 77, 516-518.	3.3	27
8	Molecular Dynamics Study of the Self-Diffusion of Ions in B ₂ O ₃ Melt at High Pressure. Journal of Physical Chemistry A, 2001, 105, 7973-7978.	2.5	16
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17	Mechanical strength and coordination defects in compressed silica glass: Molecular dynamics simulations. Physical Review B, 2007, 75, .	3.2	91
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20	Coesite and quartz characteristic of crystallization from shock-produced silica melt in the Xiuyan crater. Earth and Planetary Science Letters, 2010, 297, 306-314.	4.4	28
21	Enhanced one dimensional mobility of oxygen on strained LaCoO ₃ (001) surface. Journal of Materials Chemistry, 2011, 21, 18983.	6.7	64
22	Brittle to Ductile Transition in Densified Silica Glass. Scientific Reports, 2014, 4, 5035.	3.3	119
23	Impact of pressure on the structure of glass and its material properties. MRS Bulletin, 2017, 42, 734-737.	3.5	16
24	Densification Mechanisms of Oxide Glasses and Melts. , 2018, , 343-369.		10
25	First-principles study of pressure and SiO ₂ -incorporation effect on dynamical properties of silicon oxide. Japanese Journal of Applied Physics, 2019, 58, 111004.	1.5	2